



3N60-TC2

Power MOSFET

3A, 650V N-CHANNEL POWER MOSFET

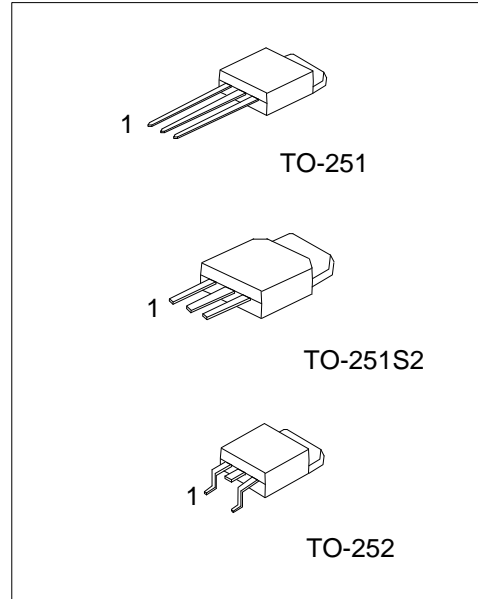
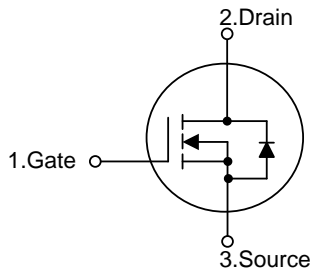
DESCRIPTION

The UTC 3N60-TC2 is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient AC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} \leq 3.0 \Omega @ V_{GS} = 10 V, I_D = 1.5A$
- * High Switching Speed

SYMBOL



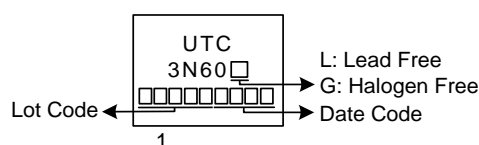
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
3N60L-TM3-T	3N60G-TM3-T	TO-251	G	D	S	Tube
3N60L-TMS2-T	3N60G-TMS2-T	TO-251S2	G	D	S	Tube
3N60L-TN3-R	3N60G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>3N60G-TM3-T</p> <p>(1) Packing Type (2) Package Type (3) Green Package</p>	<p>(1) T: Tube, R: Tape Reel (2) TM3: TO-251, TMS2: TO-251S2, TN3: TO-252 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	650	V
Gate-Source Voltage		V _{GSS}	± 30	V
Drain Current	Continuous	I _D	3	A
	Pulsed (Note 2)	I _{DM}	6	A
Avalanche Energy	Single Pulsed (Note 3)	E _{AS}	80	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4	V/ns
Power Dissipation		P _D	45	W
Junction Temperature		T _J	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

- Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
 2. Repetitive Rating: Pulse width limited by maximum junction temperature.
 3. L = 10mH, I_{AS} = 4.0A, V_{DD} = 50V, R_G = 25 Ω Starting T_J = 25°C
 4. I_{SD} ≤ 3.0A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ _{JA}	110	°C/W
Junction to Case	θ _{JC}	2.77 (Note)	°C/W

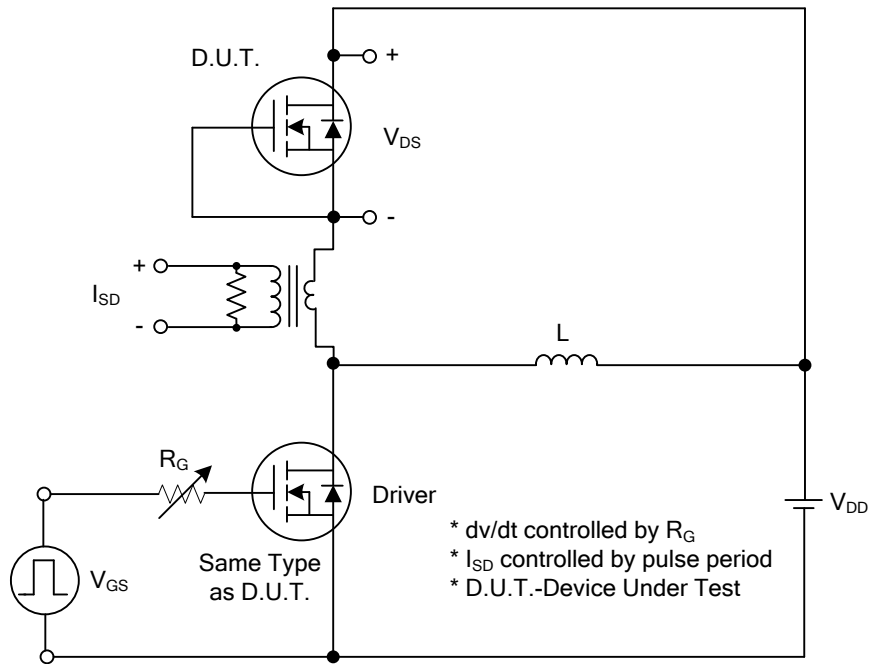
Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

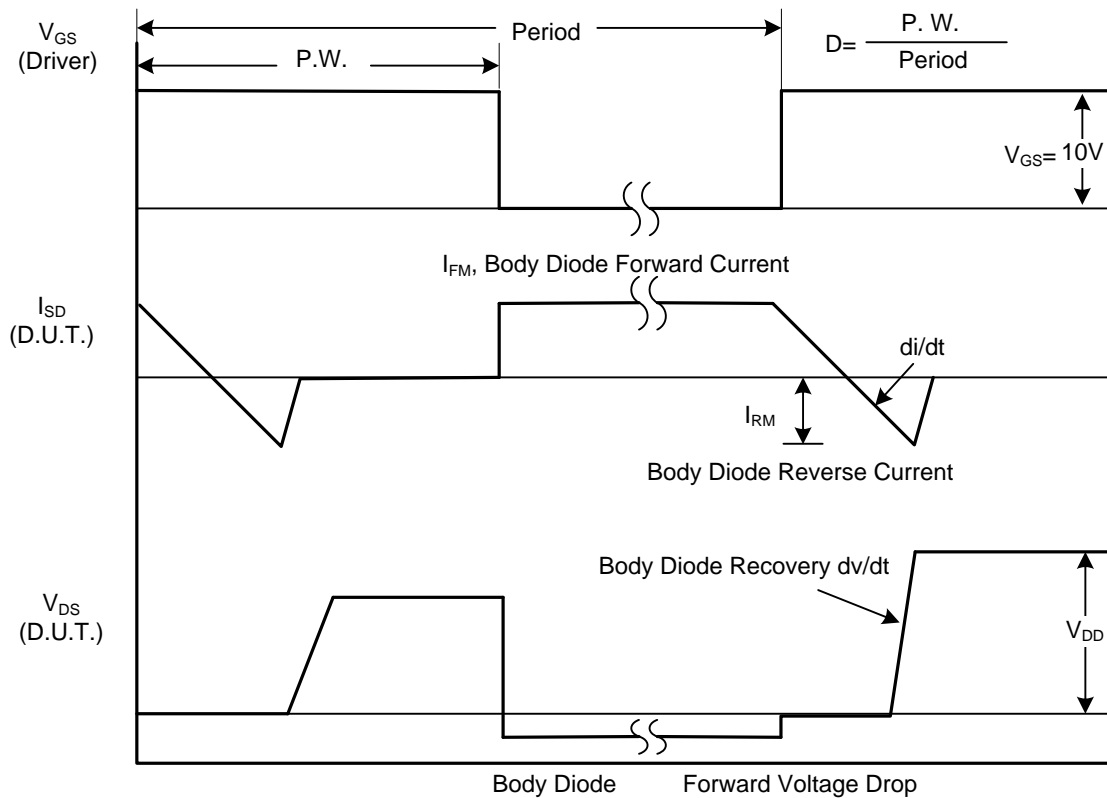
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D = 250μA	650			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =650V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	I _{GSS}	Forward			100	nA
		Reverse			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =1.5A			3.0	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0 MHz		410		pF
Output Capacitance	C _{OSS}			51		pF
Reverse Transfer Capacitance	C _{RSS}			2.8		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q _G	V _{DS} =480V, V _{GS} =10V, I _D =3A I _G =1mA (Note 1, 2)		10		nC
Gate-source Charge	Q _{GS}			4.5		nC
Gate-Drain Charge	Q _{GD}			3.3		nC
Turn-on Delay Time (Note 1)	t _{D(ON)}	V _{DS} =100V, V _{GS} =10V, I _D =3.0A, R _G =25Ω (Note 1, 2)		8		ns
Rise Time	t _R			18		ns
Turn-off Delay Time	t _{D(OFF)}			20		ns
Fall-Time	t _F			19		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I _S				3	A
Maximum Body-Diode Pulsed Current	I _{SM}				6	A
Drain-Source Diode Forward Voltage (Note 1)	V _{SD}	V _{GS} =0V, I _S =3.0A			1.4	V
Reverse Recovery Time (Note 1)	t _{rr}	V _{GS} =0V, I _S =3.0A,		250		ns
Reverse Recovery Charge	Q _{rr}	dI _F /dt=100A/μs (Note1)		1.6		μC

- Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.
 2. Essentially independent of operating temperature.

TEST CIRCUITS AND WAVEFORMS

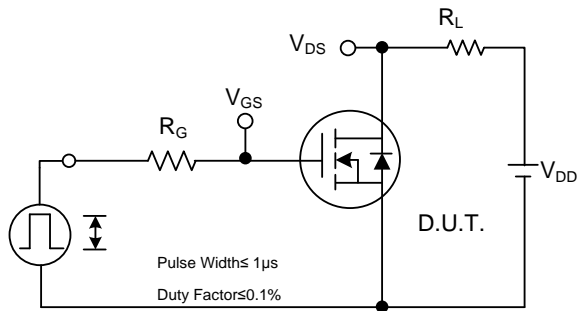


Peak Diode Recovery dv/dt Test Circuit

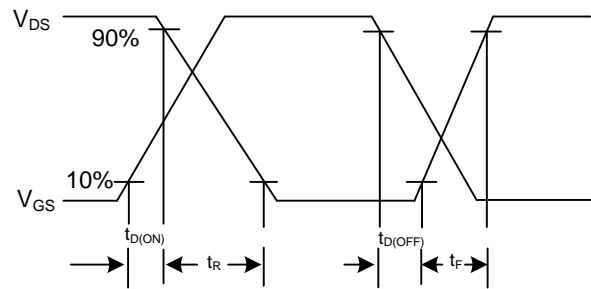


Peak Diode Recovery dv/dt Waveforms

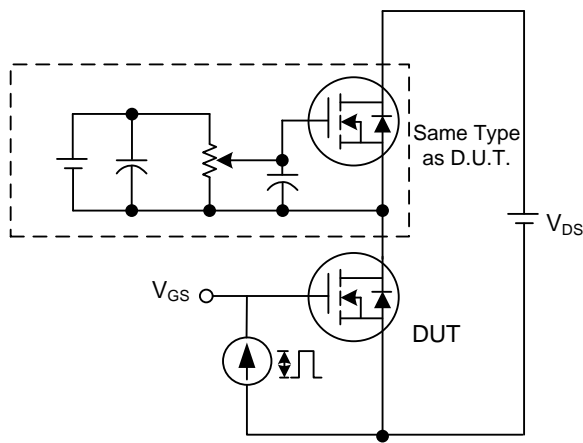
TEST CIRCUITS AND WAVEFORMS



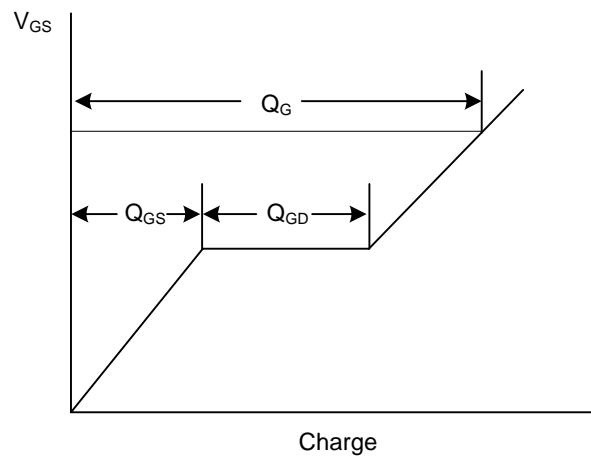
Switching Test Circuit



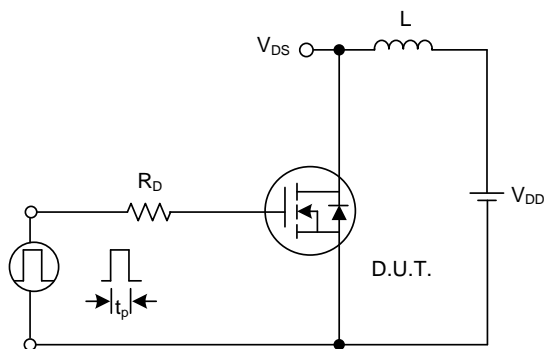
Switching Waveforms



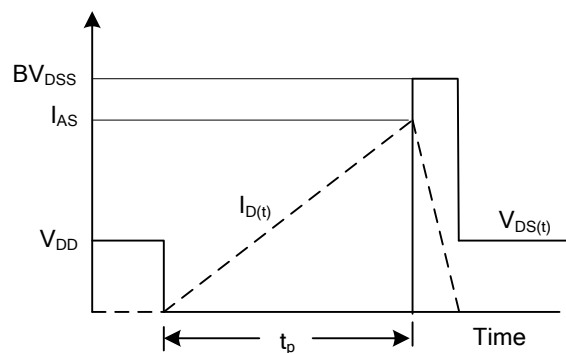
Gate Charge Test Circuit



Gate Charge Waveform

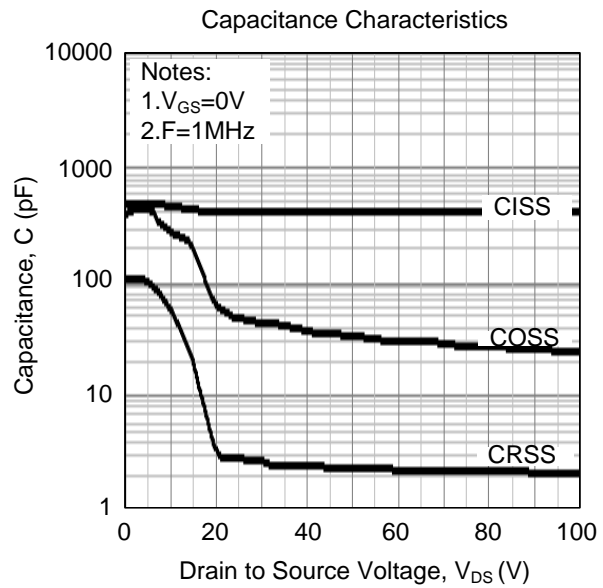
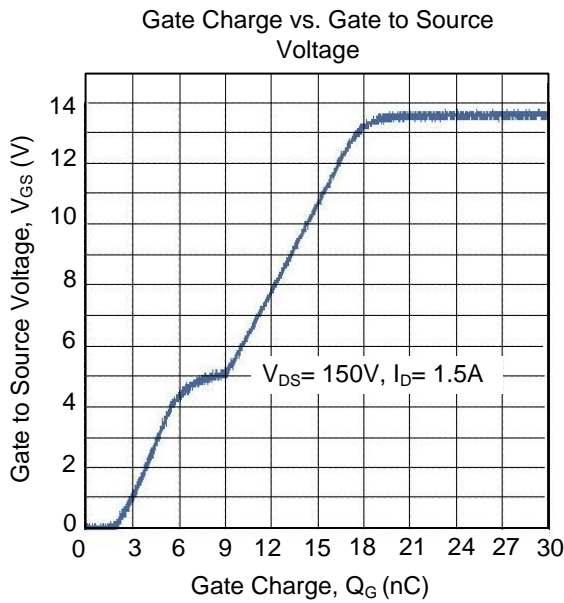


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



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